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(54) **ORGANIC LIGHT-EMITTING DIODE  
STRUCTURE AND DISPLAY DEVICE**

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**ABSTRACT**

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The present disclosure provides an organic light-emitting diode structure and a display device. In the organic light-emitting diode structure, the light-emitting layer, the hole blocking layer and the electron blocking layer satisfy the following conditions: T1 (HBL)>T1 (Host); T1 (EBL)>T1 (Host); T1 (Dopant)>T1 (Host); S1 (Host)>S1 (Dopant); wherein T1 (HBL) is the lowest triplet energy of the hole blocking layer material, T1 (Host) is the lowest triplet energy of the host material, T1 (EBL) is the lowest triplet energy of the electron blocking layer material, T1 (Dopant) is the lowest triplet energy of the guest material, S1 (Host) is the lowest singlet energy of the host material, and S1 (Dopant) is the lowest singlet energy of the guest material.

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